

2N6676, 2N6677, 2N6678, RJH6676, RJH6677, RJH6678

File Number 1165

15-A SwitchMax Power Transistors

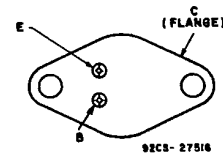
High-Voltage N-P-N Types for Off-Line Power Supplies and Other High-Voltage Switching Applications

Features:

- Fast switching speed
- High voltage ratings:
 $V_{CEX} = 350 \text{ V to } 450 \text{ V}$
- Low $V_{CE(sat)}$ at $I_C = 15 \text{ A}$

Applications:

- Off-line power supplies
- High-voltage inverters
- Switching regulators

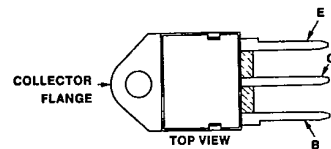
TERMINAL DESIGNATIONS

JEDEC TO-204AA

2N6676
2N6677
2N6678

The RCA 2N6676, 2N6677 and 2N6678, RJH6676, RJH6677, and RJH6678 SwitchMax series of silicon n-p-n power transistors feature high-voltage capability, fast switching speeds, and low saturation voltages, together with high safe-operating-area (SOA) ratings. They are specially designed for off-line power supplies, converter circuits, and pulse-width-modulated regulators. These high-voltage, high-speed transistors are tested for parameters that are essential to the design of high-power switching circuits. Switching times, including inductive turn-off time, and saturation voltages are specified at 100°C to provide information necessary for worst-case design.

The 2N6676, 2N6677, and 2N6678 transistors are supplied in steel JEDEC TO-204AA hermetic packages. The RJH6676, RJH6677, and RJH6678 transistors are supplied in JEDEC TO-218AC plastic packages.



JEDEC TO-218AC

RJH6676
RJH6677
RJH6678**MAXIMUM RATINGS, Absolute-Maximum Values:**

	RJH6676	RJH6677	RJH6678	2N6676	2N6677	2N6678	
* V_{CEV}							V
$V_{BE} = -1.5 \text{ V}$	450	550	650	450	550	650	
* V_{CEX} (Clamped)							V
$V_{BE} = -1.5 \text{ V}$	350	400	450	350	400	450	
* V_{CEO}	300	350	400	300	350	400	V
* V_{EBO}				8			V
$I_C(sat)$				15			A
* I_C				15			A
I_{CM}				20			A
* I_B				5			A
* P_T				175			W
T_C up to 25°C					1		W/°C
T_C above 25°C, derate linearly		1.4					
* T_{stg}, T_J		-65 to 150			-65 to 200		°C
* T_L							
At distance $\geq 1/16$ in. (1.58 mm) from seating plane for 10 s max.					235		°C
T_L							
At distance $\geq 1/8$ in. (3.17 mm) from seating plane for 10 s max.		235					°C

* In accordance with JEDEC registration data (2N6676, 2N6677, 2N6678 only).

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ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	TEST CONDITIONS				LIMITS						UNITS
	VOLTAGE V dc		CURRENT A dc		2N6676 RJH6676		2N6677 RJH6677		2N6678 RJH6678		
	V _{CE}	V _{BE}	I _C	I _B	Min.	Max.	Min.	Max.	Min.	Max.	

T_C=25°C

I _{CEV}	450 550 650	-1.5 -1.5 -1.5			—	0.1	—	—	—	—	mA
I _{EBO}		-8	0		—	2	—	2	—	2	
V _{CEO(SUS)} ^b			0.2 ^a	0	300	—	350	—	400	—	V
h _{FE}	3		15 ^a		8	—	8	—	8	—	
V _{BE(sat)}			15 ^a	3	—	1.5	—	1.5	—	1.5	V
V _{CE(sat)}			15 ^a	3	—	1	—	1	—	1	
V _{CE(sat)}			15 ^a	3	—	1.5	—	1.5	—	1.5	
V _{CEX} ^b (Clamped E _{S(B)}) L=50 μH, R _{BB} =2 Ω		-6	15	3	350	—	400	—	450	—	
I _{S(B)}	30 100		5.9 0.25		1 1	—	1 1	—	1 1	—	s
h _{FE} f=5 MHz	10		1		3	10	3	10	3	10	
f _T	10		1		15	50	15	50	15	50	MHz
C _{obo} f=0.1 MHz	10 ^c				150	500	150	500	150	500	pF
t _d ^d		-6	15	3	—	0.1	—	0.1	—	0.1	μs
t _r ^d		-6	15	3	—	0.6	—	0.6	—	0.6	
t _s ^d		-6	15	3 ^e	—	2.5	—	2.5	—	2.5	
t _f ^d		-6	15	3 ^e	—	0.5	—	0.5	—	0.5	
t _c ^f V _{CC} =200 V, L=50 μH, R _C ≤ 13.5 Ω		-6	15	3 ^e	—	0.5	—	0.5	—	0.5	

T_C=100°C

I _{CEV}	450 550 650	-1.5 -1.5 -1.5			—	1	—	—	—	—	mA
V _{CE(sat)}			15 ^a	3	—	2	—	2	—	2	V
t _d ^d		-6	15	3	—	1	—	1	—	1	μs
t _r ^d		-6	15	3 ^e	—	4	—	4	—	4	
t _s ^d		-6	15	3 ^e	—	1	—	1	—	1	
t _c ^f V _{CC} =200 V, L=50 μH, R _C ≤ 13.5 Ω		-6	15	3 ^e	—	0.8	—	0.8	—	0.8	

R _{θJC} 2N6676, 2N6677, 2N6678	10		5		—	1	—	1	—	1	°C/W
R _{θJC} RJH6676, RJH6677, RJH6678	10		5		—	0.71	—	0.71	—	0.71	°C/W

^aPulsed: pulse duration=300 μs, duty factor ≤ 2%.

^bCAUTION: The sustaining voltage V_{CEO(SUS)} and V_{CEX} MUST NOT be measured on a curve tracer.

^cIn accordance with JEDEC registration data (2N6676, 2N6677, 2N6678 only).

^dV_{CE} value.

^eV_{CC}=200 V, t_p=20 μs.

^fI_{B1}=-I_{B2}.

^gCollector clamped to V_{CEX}.

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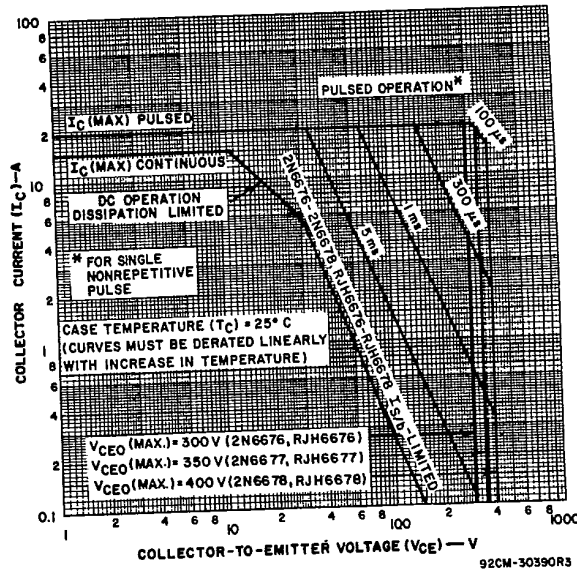


Fig. 1 - Maximum operating areas for all types ($T_c = 25^\circ\text{C}$).

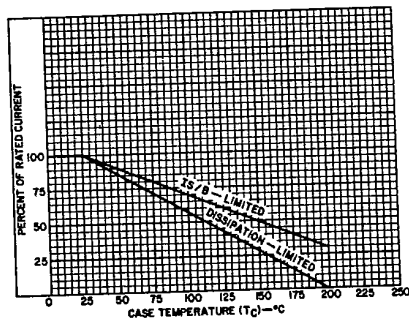


Fig. 2 - Dissipation and I_{ds} derating curves for 2N6676, 2N6677, and 2N6678.

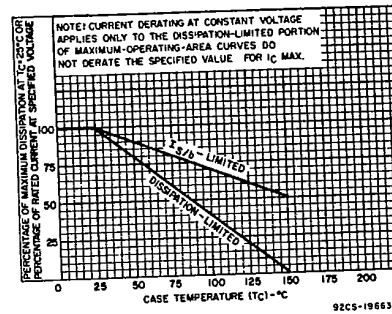


Fig. 3 - Dissipation and I_{ds} derating curves for RJH6676, RJH6677, and RJH6678.

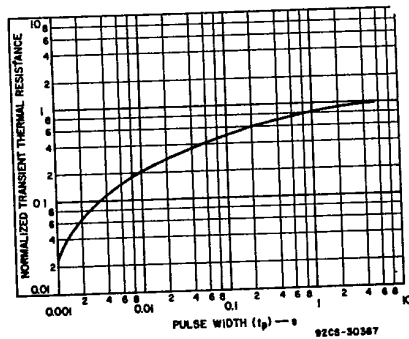


Fig. 4 - Typical thermal-response characteristic for all types.

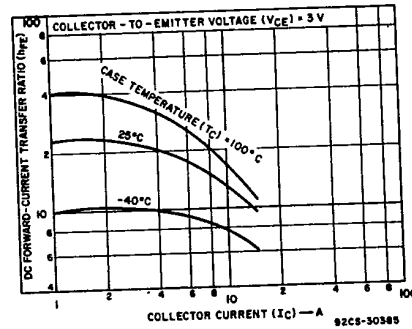


Fig. 5 - Typical dc beta characteristics for all types.

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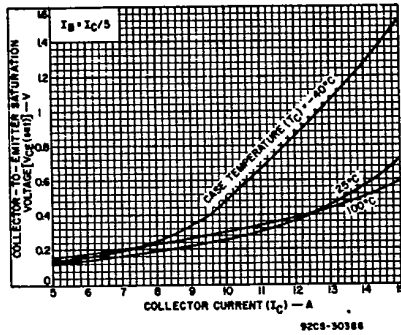


Fig. 6 - Typical collector-to-emitter saturation voltage characteristics for all types.

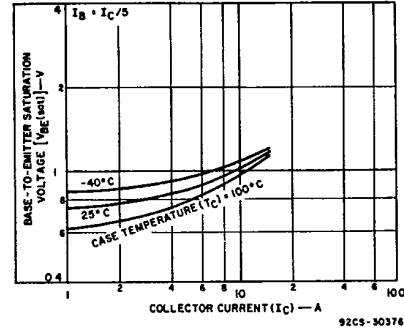


Fig. 7 - Typical base-to-emitter saturation voltage characteristics for all types.

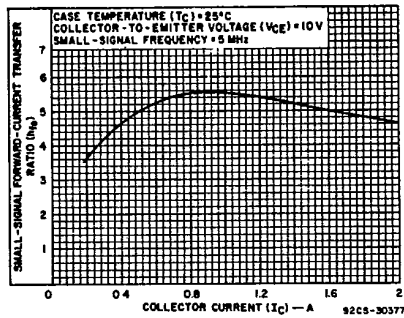


Fig. 8 - Typical small-signal forward current transfer ratio characteristic for all types ($f = 5$ MHz).

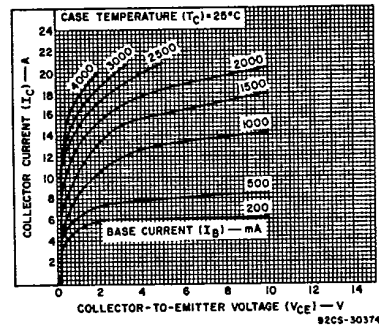


Fig. 9 - Typical output characteristics for all types.

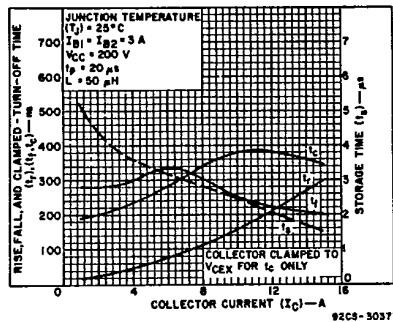


Fig. 10 - Typical saturated-switching-time characteristics at $T_J = 25^\circ\text{C}$ as a function of collector current for all types.

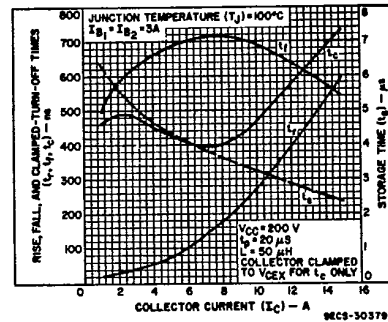


Fig. 11 - Typical saturated-switching-time characteristics at $T_J = 100^\circ\text{C}$ as a function of collector current for all types.

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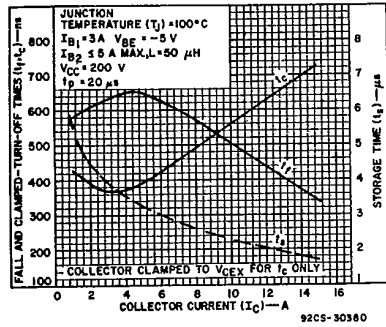


Fig. 12 - Typical saturated-switching-time characteristics at $T_j = 100^\circ\text{C}$ as a function of collector current for all types.

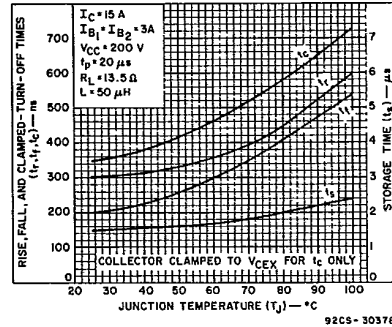


Fig. 13 - Typical saturated-switching-time characteristics as a function of junction temperature for all types.

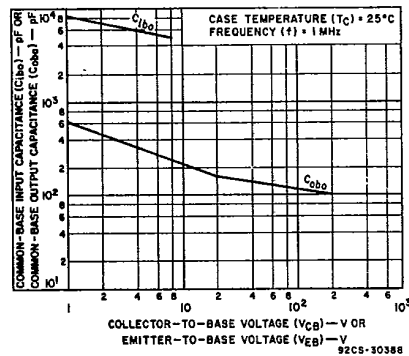


Fig. 14 - Typical common-base input (C_{ibo}) or output (C_{obo}) capacitance characteristics for all types.

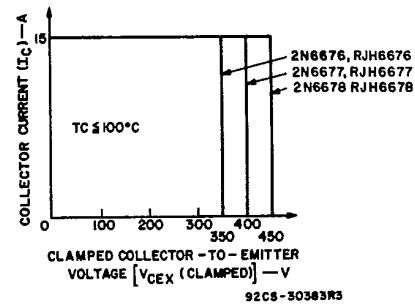


Fig. 15 - Maximum operating conditions for switching between saturation and cutoff for all types.

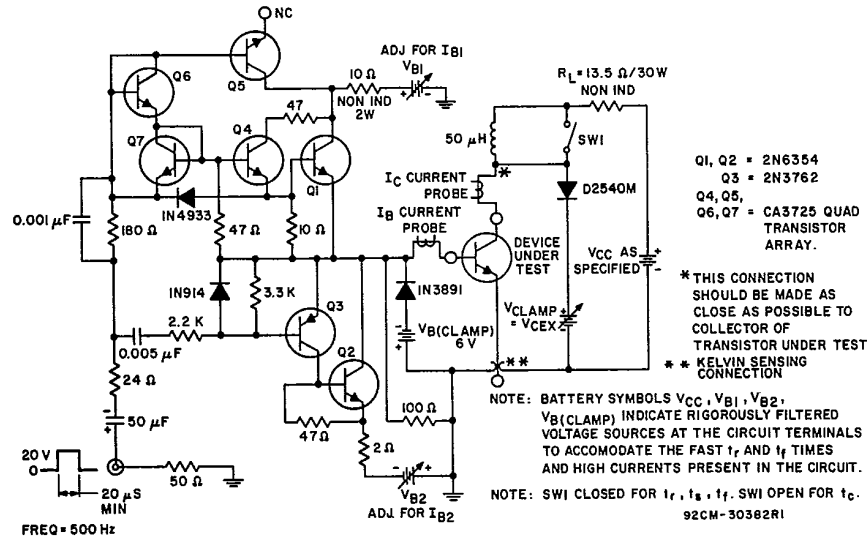


Fig. 16 - Circuit for measurement switching times.

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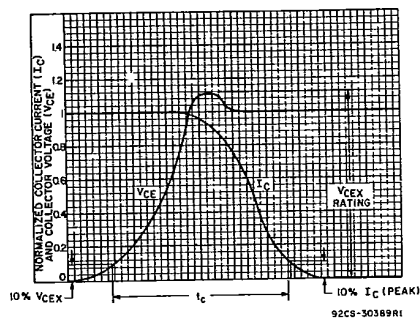


Fig. 17 - Oscilloscope display for normalized measurement of clamped inductive switching time (t_c).

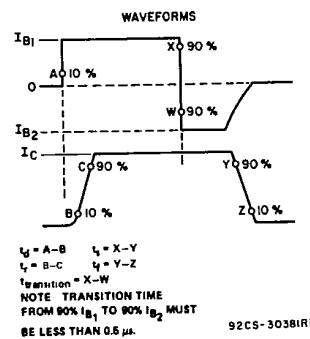


Fig. 18 - Phase relationship between input and output currents showing reference points for specification of switching times.